A 60nm CMOS, 3rd and 5th Order Low Pass Filter with Higher Cut-off Frequency

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Abstract
The design of CMOS based low pass filter for analog-to-digital, digital-to-analog and audio applications is described in this paper. Active load resistor and floating inductor is used for the implementation of low pass filter. CMOS technology has become dominant over bipolar technology for analog circuits design in mixed signal system. The differential floating active inductor is designed with CMOS and current sources. The floating inductor may be electronically tuned by varying external bias voltage as well as current. The simulations are obtained by using 65nm CMOS technology on Tanner EDA tool 13.0. The filters are synthesized from 3rd and 5th order low-pass LC prototype and designed using ladder structure.

Keywords: Complementary Metal Oxide Semiconductor (CMOS), low pass filter (LPF), active resistor, Power delay product (PDP).

1. Introduction
The improvement of scaled VLSI technologies, associated with the demand for signal processing integrated in a single chip, has extremely good ability for design of analog circuits. Mostly the VLSI circuits in analog consist of amplifiers, filters, oscillators, digital to analog converters and analog to digital converter [1] [2]. The key driving factor for any system is high gain, high packing density, low power dissipation, easy in designing etc. The most important part in analog circuit that should be integrated is analog filters [3] [4]. The performance of general purpose processor and digital signal processing unit has been increased by scaling of CMOS technologies. Advanced and scalable CMOS technologies provide low cost, high integration and good reliability which form digital and analog circuit in a single chip [5] [6].

Filters especially analog filters has a wide range of applications in different areas such as in control system, communication system, military, radar, medical instruments and industrial electronics [7] [8]. Filter is a circuit that transforms an electrical signal at input in such a manner so that the output signal has specified features which may be in terms of frequency or in time domain depending upon the application. Filter is the circuit that works on signal in a frequency dependent manner [9] [10].

The fundamental nature of a filter can be described by evaluating the frequency dependent behavior of the impedance of inductor and capacitor [11] [12]. Filters can be made from passive components and from active components. Filters that are fabricated from active components have large number of advantages over filters fabricated with passive components. Passive inductor is large in size, unable to work at moderate frequency range; standard values are not very close to each other [13] [14]. So active inductor is preferred for the designing of filters. In this paper section 2 describes proposed active inductor, 3rd and 5th order filters using active inductor. Section 3 gives the experimental results. Conclusion is in section 4.

2. Filters
Proposed differential floating active inductor was designed with the help of CMOS and current sources that was shown in Fig. 1 (a) and the schematic shown in fig. 1 (b) is of conventional inductor. Proposed active inductor was designed with 7 CMOS which include 4 NMOS from M1 to M4 and 3 PMOS from M5 to M7. Cross-coupled pair was formed by M1 and M2, from dc point of view and transistors M3 and M4 are in common drain configuration. The above circuit works as an inductor at the input voltage $V_{in}$. At the quiescent bias point, transistors M1 to M4 are saturated. Depending on the controlled voltages $V_d$ and $V_{bb}$ at the gates transistors M5, M6 and M7 they work in linear region or in saturation region. Therefore at desired bias point M5, M6 and M7 are modeled as $g_{ds5}$, $g_{ds5'}$ $g_{ds6}$ and $g_{ds7}$ representing the drain conductance. In this paper conventional inductor is the inductor that was proposed by Lu et al. [15]. In fig. 2 (a) small-signal model for the proposed active inductor in simplified manner is shown, and fig. 2(b) shows the equivalent impedance circuit of active inductor. Small-signal analysis is done for the approximate analysis of a circuit [16] [17]. For an input current $I_{in}$, the input voltage is $V_{in}$ for the differential port input impedance $Z_{in}$ is given below:

$$Z_{in} = \frac{v_{in}}{i_{in}} = \frac{\left[j\omega (C_{gs1} + C_{gs3}) - g_{m1} + g_{ds5}\right]}{g_{ds5}[g_{m1} + g_{m3} + j\omega (C_{gs1} + C_{gs3})]}$$ (1)
By solving it with approximation the value of inductance Leq can be expressed as:

$$L_{eq} = \frac{(C_{gs1} + C_{gs3})}{g'_{ds5} (2g_{m1} + g_{m3} - g'_{ds5})} \quad (2)$$

Where g’d’s5 is expressed as:

$$g'_{ds5} = \frac{(g_{ds7} + g_{dss}M_1)g_{dss}}{g_{ds7} + g_{dss}M_1 + g_{dss}} \quad (3)$$

Where gds6M1 and gds6M2 are given as:

$$g_{dss}M_1 = \frac{g_{dss}}{1 - K} \quad (4)$$

And

$$g_{dss}M_2 = \frac{g_{dss}K}{1 - K} \quad (5)$$

The Miller constant K is expressed as:

The equivalent inductance depend on Cgs1, Cgs3, gm1, gm3 and g’d’s5 this was observed from equation (2). By manipulating the drain conductance by gate voltage, tuning of inductance can be achieved. Therefore, for tuning of active inductor Vb and Vbb can be used as the controlling element.

Filters can be designed up to any limit their designing will depend on its application in which it was used. But as we increase the order it will also increase the number of components used in it due to this size of the filter will also increase. Therefore higher order filter are complex in designing and very expensive. The schematic for third order RLC low pass filter is shown in fig.3. For describing the electronically tunable feature of inductor, 3rd order low pass filter using active components as shown in fig.4 has been implemented, with capacitance C of 1p and current sources of 10µA. Bias currents IB1 and IB2 are varied for different values such as 5µA and 15µA. Its bias voltage Vb is also varied from 0.7 to 0.9V with the difference of 0.05V to varying the transconductance of the CMOS.

To show the flexibility of active inductor in filters, fifth-order low pass filter has been designed. Fig. 5 shows the LC ladder topology for 5th order low pass filter with passive components and fig. 6 shows the 5th order low pass filter designed with active floating inductor and active load resistor.

3. Experimental Results

3rd and 5th order low pass filter designed with proposed floating inductor was analyzed by the use TSPICE. 65nm technology is used for experimental result for the circuit implemented with CMOS. Fig. 7 shows response of third order active LPF. The variations in 3dB frequencies of third order LPF w.r.t. the bias voltage (Vb) and the bias current (Ib) was shown in fig. 8. Variation of power consumption and power delay product with bias voltage for third order filter was shown in fig. 9. These figures reveal that as the filter designed with the proposed floating inductor shows better result than the conventional active inductor.

The response curve of frequency for fifth order low pass filter is shown in fig.10. It shows a 3dB frequency of 148.12MHz. Fig. 11 (a) and (b) shows the variation in 3dB frequency with bias voltage and bias current. Fig. 12 (a) and (b) shows the variation in power consumption and power delay product with bias voltage, filter with proposed inductor shows better results than the filter designed with conventional inductor. As we increase the order of filter number of components required for the formation of the circuit also increases and the cut off frequency decreases. Fig. 13 shows the response of LPF as a function of filter order it clearly shows that as we increase the order of filter it moves towards the ideal response curve. Fig. 14 (a) and (b) shows the variation 3 dB frequency with bias voltage and bias current. As the number of components increases as we increase the order of filter due to this power consumption and power delay also increases according to the order of filter, fig. 15 (a) and (b) shows the variation power consumption and power delay product with bias voltage. Table I provides the simulation results and design parameters used for 3rd and 5th order low pass filter.

4. Conclusion

Depending upon the application and given conditions there are various methods for the designing of a filter. A floating inductor using 7-CMOSs with two current sources has been proposed. In this paper 65nm CMOS technology is used. With the assist of external bias voltage and bias current the inductance of an inductor is regulate. It was analyzed that the proposed circuit provide enough accuracy due to this it is applicable for the designing of 3rd and 5th order low pass filter. Experimental results shows that the higher order filter designed with proposed floating inductor shows better results than the convention filter.

References

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Acknowledgment
The authors Suman Nehra and P. K. Ghosh thankfully acknowledge the authority of College of Engineering and Technology, Mody University of Science and Technology, Lakshmangarh for providing the opportunity to use the resources of the Institute. I express my deep sense of gratitude towards Ms. Priyanka Soni, Junior Engineer, Jd. V. V. N. L., Bikaner for her continuous support.

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Fig. 1. (a) Proposed active inductor (b) Conventional active inductor

Fig. 2. (a) Proposed active inductor with small signal model (b) Proposed active inductor with equivalent circuit

Fig. 3. Third-order low pass filter topology
Fig. 4. 3\textsuperscript{rd} Order LPF using active inductor

Fig. 5. Fifth-order low pass filter topology

Fig. 6. 5\textsuperscript{th} Order LPF using active inductor
Fig. 7. Response of 3rd order LPF

Fig. 8. (a) Variation in 3dB frequency with bias voltage (b) Variation in 3dB frequency with bias current for 3rd order LPF

Fig. 9. (a) Variation in power consumption with bias voltage (b) Variation in PDP with bias voltage for 3rd order
Fig. 10. Response of 5th order LPF

Fig. 11. (a) Variation in 3dB frequency with bias voltage (b) Variation in 3dB frequency with bias current for 5th order LPF

Fig. 12. (a) Variation in power consumption with bias voltage (b) Variation in PDP with bias voltage for 5th order LPF
Fig. 13. Response of LPF as a function of filter order

Fig. 14. (a) Variation in 3dB frequency with bias voltage (b) Variation in 3dB frequency with bias current according to the order of filter

Fig. 15. (a) Variation power consumption with bias voltage (b) Variation in power delay product with bias according to the order of filter
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<thead>
<tr>
<th>S.No.</th>
<th>Design Parameters</th>
<th>Values</th>
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<tbody>
<tr>
<td>1.</td>
<td>Supply Voltage (V&lt;sub&gt;DD&lt;/sub&gt;)</td>
<td>1V</td>
</tr>
<tr>
<td>2.</td>
<td>Bias Voltage (V&lt;sub&gt;b&lt;/sub&gt;)</td>
<td>0.7V</td>
</tr>
<tr>
<td>3.</td>
<td>Supply Voltage (V&lt;sub&gt;bb&lt;/sub&gt;)</td>
<td>0.5V</td>
</tr>
<tr>
<td>4.</td>
<td>C&lt;sub&gt;1&lt;/sub&gt; = C&lt;sub&gt;2&lt;/sub&gt; = C&lt;sub&gt;3&lt;/sub&gt;</td>
<td>1p</td>
</tr>
<tr>
<td>5.</td>
<td>Current sources</td>
<td>10uA</td>
</tr>
<tr>
<td>6.</td>
<td>Resistance R&lt;sub&gt;1&lt;/sub&gt;</td>
<td>1KΩ</td>
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<tr>
<td>7.</td>
<td>Cut off frequency for 3&lt;sup&gt;rd&lt;/sup&gt; order proposed LPF</td>
<td>166.04MHz</td>
</tr>
<tr>
<td>8.</td>
<td>Cut off frequency for 5&lt;sup&gt;th&lt;/sup&gt; order proposed LPF</td>
<td>148.12 MHz</td>
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